Takeshi Kanashima

List of Publications by Year in descending order

Source: https://exaly.com/author-pdf/211616/publications.pdf Version: 2024-02-01



#	Article	IF	CITATIONS
1	Enhancement of electrical properties in polycrystalline BiFeO3 thin films. Applied Physics Letters, 2006, 89, 192902.	3.3	157
2	Tactile sensor array using microcantilever with nickel–chromium alloy thin film of low temperature coefficient of resistance and its application to slippage detection. Sensors and Actuators A: Physical, 2012, 186, 32-37.	4.1	69
3	A pseudo-single-crystalline germanium film for flexible electronics. Applied Physics Letters, 2015, 106, .	3.3	44
4	Structural and ferroelectric properties of epitaxial Bi5Ti3FeO15 and natural-superlattice-structured Bi4Ti3O12–Bi5Ti3FeO15 thin films. Journal of Applied Physics, 2010, 108, .	2,5	42
5	Pulsed Laser Deposition and Characterization of Sr and Zn Co-Substituted BiFeO ₃ Thin Films. Japanese Journal of Applied Physics, 2009, 48, 09KB03.	1.5	27
6	Electrical properties of pseudo-single-crystalline Ge films grown by Au-induced layer exchange crystallization at 250 °C. Journal of Applied Physics, 2018, 123, 215704.	2.5	24
7	Photoluminescence of SiO2 films grown by photo-induced chemical vapor deposition. Applied Surface Science, 1994, 79-80, 321-326.	6.1	23
8	Spin transport in <i>p</i> -Ge through a vertically stacked Ge/Fe3Si junction. Applied Physics Letters, 2016, 109, .	3.3	23
9	Stability Improvement of Tactile Sensor of Normal and Shear Stresses Using Ni-Cr Thin Film Gauge. IEEJ Transactions on Sensors and Micromachines, 2009, 129, 411-416.	0.1	22
10	Fabrication and Normal/Shear Stress Responses of Tactile Sensors of Polymer/Si Cantilevers Embedded in PDMS and Urethane Gel Elastomers. IEEJ Transactions on Sensors and Micromachines, 2008, 128, 193-197.	0.1	20
11	Ferroelectric and structural properties of stress-constrained and stress-relaxed polycrystalline BiFeO3 thin films. Journal of Applied Physics, 2009, 105, 061617.	2.5	20
12	A crystalline germanium flexible thin-film transistor. Applied Physics Letters, 2017, 111, .	3.3	20
13	Basic characteristics of metal-ferroelectric-insulator-semiconductor structure using a high-k PrOx insulator layer. Journal of Applied Physics, 2003, 93, 4137-4143.	2.5	19
14	Tactle array sensor with inclined chromium/silicon piezoresistive cantilevers embedded in elastomer. , 2009, , .		18
15	Organic ferroelectric gate field-effect transistor memory using high-mobility rubrene thin film. Japanese Journal of Applied Physics, 2014, 53, 04ED11.	1.5	17
16	All-epitaxial Co2FeSi/Ge/Co2FeSi trilayers fabricated by Sn-induced low-temperature epitaxy. Journal of Applied Physics, 2016, 119, .	2.5	17
17	3æ−¹åʿā,«āf³āfēf¬āfēf¼ā,'用ā,aŸåਝè»,ė§¦è¦šā,»āf³ā,µā®ä¼œè£½ãë基çŽç‰¹æ€§. IEEJ Transactions o 	on Se os ors a	and ı∀ licromac

Active Touch Sensing by Multi-axial Force Measurement Using High-Resolution Tactile Sensor with Microcantilevers. IEEJ Transactions on Sensors and Micromachines, 2014, 134, 58-63.

0.1 16

ΤΑΚΕSΗΙ ΚΑΝΑSΗΙΜΑ

#	Article	IF	CITATIONS
19	Optical characterizations of photoâ€induced chemical vapor deposition produced SiO2films in vacuum ultraviolet, ultraviolet, and visible region. Journal of Applied Physics, 1993, 74, 5742-5747.	2.5	15
20	Fabrication and Characterization of Ferroelectric Poly(vinylidene fluoride–tetrafluoroethylene) Gate Field-Effect Transistor Memories. Japanese Journal of Applied Physics, 2010, 49, 04DD14.	1.5	15
21	Multimodal measurement of proximity and touch force by light- and strain-sensitive multifunctional MEMS sensor. , 2014, , .		15
22	Ferroelectric Properties of Bi _{1.1} Fe _{1-x} Co _x O ₃ Thin Films Prepared by Chemical Solution Deposition Using Iterative Rapid Thermal Annealing in N ₂ and O ₂ . Japanese Journal of Applied Physics, 2010, 49, 09MB05.	1.5	14
23	Fabrication and Characterization of Ferroelectric Gate Field-Effect Transistor Memory Based on Ferroelectric–Insulator Interface Conduction. Japanese Journal of Applied Physics, 2006, 45, 8608-8610.	1.5	12
24	Preparation of BiFeO\$_{3}\$ Thin Films on SrRuO\$_{3}\$/SrTiO\$_{3}\$(001) Substrate by Dual Ion Beam Sputtering. Japanese Journal of Applied Physics, 2011, 50, 09NB01.	1.5	12
25	Spin-related thermoelectric conversion in lateral spin-valve devices with single-crystalline Co ₂ FeSi electrodes. Applied Physics Express, 2015, 8, 043003.	2.4	12
26	Nondestructive and Contactless Monitoring Technique of Si Surface Stress by Photoreflectance. Japanese Journal of Applied Physics, 2001, 40, 2844-2848.	1.5	11
27	Crosstalk Reduction of Tactile Sensor Array with Projected Cylindrical Elastomer over Sensing Element. Japanese Journal of Applied Physics, 2011, 50, 06GM08.	1.5	11
28	Proximity and Tactile Sensing Using a Single MEMS Sensor with Photo- and Strain Sensitivities. IEEJ Transactions on Sensors and Micromachines, 2014, 134, 229-234.	0.1	11
29	Fabrication and Characterization of Silicon-Polymer Beam Structures for Cantilever-Type Tactile Sensors. , 2007, , .		10
30	Characteristics improvement of HfO2/Ge gate stack structure by fluorine treatment of germanium surface. Applied Surface Science, 2008, 254, 6932-6936.	6.1	10
31	Multiferroic properties of polycrystalline Zn-substituted BiFeO3 thin films prepared by pulsed laser deposition. Current Applied Physics, 2011, 11, S270-S273.	2.4	10
32	Preparation of BiFe _{0.9} Co _{0.1} O ₃ Films by Pulsed Laser Deposition under Magnetic Field. Japanese Journal of Applied Physics, 2011, 50, 09NB03.	1.5	10
33	Ferroelectric and Piezoelectric Properties of Polycrystalline BiFeO ₃ Thin Films Prepared by Pulsed Laser Deposition under Magnetic Field. Japanese Journal of Applied Physics, 2012, 51, 09MD05.	1.5	10
34	Fabrication and Noise Reduction of the Miniature Tactile Sensor Using Through-Silicon-Via Connection with Signal Amplifier. Japanese Journal of Applied Physics, 2013, 52, 06GL08.	1.5	10
35	Electronic characterization of Si/SiO2 structure using photo-CVD SiO2 thin film on atomically flat Si substrate. Applied Surface Science, 1998, 130-132, 214-220.	6.1	8
36	Influences of perforation ratio in characteristics of capacitive micromachined ultrasonic transducers in air. Sensors and Actuators A: Physical, 2011, 171, 191-198.	4.1	8

#	Article	IF	CITATIONS
37	Characterization of epitaxial BiFeO3 thin films prepared by ion beam sputtering. Current Applied Physics, 2011, 11, S244-S246.	2.4	8
38	Low-temperature <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>B</mml:mi><mml:mn>2and magnetic properties of<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Fe</mml:mi><mml: on bcc alloys. Physical Review B, 2015, 92</mml: </mml:msub></mml:mrow></mml:math </mml:mn></mml:mrow></mml:math 	110> 3.2 mrow> < m	mrow> 8 ml:mn>100 </td
39	Theoretical analysis of fluorine-passivated germanium surface for high-k/Ge gate stack by molecular orbital method. Applied Surface Science, 2010, 257, 917-920.	6.1	7
40	Leakage Current Reduction and Ferroelectric Property of BiFe _{1-x} Co _x O ₃ Thin Films Prepared by Chemical Solution Deposition Using Iterative Rapid Thermal Annealing at Approximately 520 °C. Japanese Journal of Applied Physics, 2010, 49, 095803.	1.5	7
41	Photoluminescence and Its Excimer Laser Irradiation Effects in SiO2Film Prepared by Photo-Induced Chemical Vapor Deposition. Japanese Journal of Applied Physics, 1993, 32, 3113-3119.	1.5	6
42	Preparation of fluorocarbon thin film deposited by soft X-ray ablation and its electrical characteristics and thermal stability. Applied Surface Science, 2006, 252, 7774-7780.	6.1	6
43	IMPROVEMENT OF MEMORY RETENTION IN METAL-FERROELECTRIC-INSULATOR-SEMICONDUCTOR STRUCTURE BY SrBi2Ta2O9 SURFACE MODIFICATION INDUCED BY NITROGEN AND OXYGEN RADICAL IRRADIATION. Integrated Ferroelectrics, 2006, 84, 179-188.	0.7	6
44	X-ray diffraction study of polycrystalline BiFeO3 thin films under electric field. Applied Physics Letters, 2008, 93, 042907.	3.3	6
45	Organic Ferroelectric Field-Effect Transistor Memory Using Flat Poly(vinylidene) Tj ETQq1 1 0.784314 rgBT /Ove 02BK06.	erlock 10 T 1.5	f 50 427 Td (1 6
46	Identification of various kinds of papers using multi-axial tactile sensor with micro-cantilevers. , 2013, , .		6
47	Effect of atomic-arrangement matching on La2O3/Ge heterostructures for epitaxial high- <i>k</i> -gate-stacks. Journal of Applied Physics, 2015, 118, .	2.5	6
48	ENHANCEMENT OF MEMORY RETENTION TIME OF MFIS STRUCTURE WITH SBT FERROELECTRIC AND SiO ₂ BUFFER LAYERS TREATED BY NITROGEN RADICAL IRRADIATION. Integrated Ferroelectrics, 2008, 96, 27-39.	0.7	5
49	Fabrication of a Flexible Array for Tactile Sensors with Microcantilevers and the Measurement of the Distribution of Normal and Shear Forces. Japanese Journal of Applied Physics, 2011, 50, 06GM02.	1.5	5
50	Preparation of epitaxial BiFeO3 thin films on La-SrTiO3 substrate by using magnetic-field-assisted pulsed laser deposition. Journal of the Korean Physical Society, 2013, 62, 1041-1045.	0.7	5
51	Preparation and Characterization of BiFeO3 Thin Film Deposited on ITO Substrate by Using Pulsed Laser Deposition. Journal of the Korean Physical Society, 2011, 59, 2537-2541.	0.7	5
52	Review of Texture Measurement of Object Surface by Tactile Sensor with Inclined Micro-cantilevers. IEEJ Transactions on Sensors and Micromachines, 2013, 133, 147-154.	0.1	5
53	Synergistic information encoding by combinatorial pulse operation of ferroelectrics. Applied Physics Letters, 2009, 95, 202905.	3.3	4
54	Repetition Rate Dependence of Ferroelectric Properties of Polycrystalline BiFeO ₃ Films Prepared by Pulsed Laser Deposition Method. Ferroelectrics, 2013, 453, 1-7.	0.6	4

Τακές Ηι Κανασηιμα

#	Article	IF	CITATIONS
55	Columnar Growth of BiFeO ₃ Films Prepared by Magnetic-field-assisted Pulsed Laser Deposition. Ferroelectrics, 2014, 466, 63-73.	0.6	4
56	Texture measurement and identification of object surface by MEMS tactile sensor. , 2014, , .		4
57	Exchange coupling in metallic multilayers with a top FeRh layer. AIP Advances, 2016, 6, .	1.3	4
58	X-ray Diffraction Study of Electric-field-induced Strains in Polycrystalline BiFeO3 Thin Films at Low Temperature Using Synchrotron Radiation. Journal of the Korean Physical Society, 2011, 59, 2556-2559.	0.7	4
59	Miniature Ultrasonic and Tactile Sensors for Dexterous Robot. Transactions on Electrical and Electronic Materials, 2012, 13, 215-220.	1.9	4
60	Development of a Microscopic Three-Axis Tactile Sensor: Preliminary Examinations to Establish Sensing Algorithm by Using a Simulated Mockup. Lecture Notes in Computer Science, 2008, , 561-566.	1.3	4
61	Molecular orbital analysis of reaction processes of fluorine with H-terminated silicon (111) and (100) surfaces. Journal of Applied Physics, 1999, 85, 244-248.	2.5	3
62	Molecular orbital calculation of surface reaction of SnO/sub 2/ gas sensors for aminic and carboxylic smells. , 0, , .		3
63	Contactless Characterization of Fixed Charges in HfO2Thin Film from Photoreflectance. Japanese Journal of Applied Physics, 2005, 44, 2409-2414.	1.5	3
64	Preparation and characterization of HfO2thin films by photo-assisted MOCVD. European Physical Journal Special Topics, 2006, 132, 279-283.	0.2	3
65	First-Principles Study of Tetragonality Ratio and Unit-Cell Volume Influence on Spontaneous Polarization of BaTiO3 and PbTiO3. Zairyo/Journal of the Society of Materials Science, Japan, 2006, 55, 169-172.	0.2	3
66	Microwave Tunable Devices Composed of Coplanar Waveguide Line with (Ba0.6,Sr0.4)TiO3/Au/Cr/(Ba0.6,Sr0.4)TiO3Sandwich Structure. Japanese Journal of Applied Physics, 2008, 47, 7500-7504.	1.5	3
67	Mutiferroic Properties of Polycrystalline Sr-Substituted BiFeO ₃ Thin Films Prepared by Pulsed Laser Deposition. Ferroelectrics, 2011, 416, 119-124.	0.6	3
68	Improvement in the Property of Field Effect Transistor Having the HfO2/Ge Structure Fabricated by Photoassisted Metal Organic Chemical Vapor Deposition with Fluorine Treatment. Japanese Journal of Applied Physics, 2011, 50, 04DA11.	1.5	3
69	Multi-axial tactile sensor with micro-cantilever embedded in hemispherical elastomer for surface texture measurement. , 2013, , .		3
70	A low-temperature fabricated gate-stack structure for Ge-based MOSFET with ferromagnetic epitaxial Heusler-alloy/Ge electrodes. Japanese Journal of Applied Physics, 2016, 55, 063001.	1.5	3
71	A Trial of Smell Discrimination by SnO2 Gas Sensor. Zairyo/Journal of the Society of Materials Science, Japan, 2006, 55, 165-168.	0.2	3
72	Microfocusing of soft X-ray undulator light using an elliptically bent cylinder mirror. Nuclear Instruments and Methods in Physics Research, Section A: Accelerators, Spectrometers, Detectors and Associated Equipment, 2001, 467-468, 287-290.	1.6	2

#	Article	IF	CITATIONS
73	FERROELECTRIC GATE FET MEMORY BASED ON CONDUCTION OF FERROELECTRIC-INSULATOR INTERFACE. Integrated Ferroelectrics, 2007, 89, 160-170.	0.7	2
74	PREPARATION AND CHARACTERIZATION OF HAFNIUM SILICATE DIELECTRIC LAYERS BY PHOTO-ASSISTED MOCVD USING MIXED PRECURSOR OF Hf(O-t-C ₄ H ₉) ₄ AND Si(O-t-C ₄ H ₉) ₄ . Integrated Ferroelectrics, 2008, 97, 103-110.	0.7	2
75	Fabrication of tactile sensor array using microcantilever with low-TCR nickel-chromium alloy thin film for slippage detection. Procedia Engineering, 2011, 25, 627-630.	1.2	2
76	Growth of high quality BiFeO <inf>3</inf> thin films by dual ion beam sputtering. , 2011, , .		2
77	Current conduction in single-domain BiFeO ₃ thin films. Japanese Journal of Applied Physics, 2014, 53, 08NA01.	1.5	2
78	Robust spin-current injection in lateral spin valves with two-terminal Co2FeSi spin injectors. AIP Advances, 2017, 7, 055808.	1.3	2
79	Characterization of Interface States of HfO2/Ge with Fluorine Treatment by Using DLTS/ICTS. ECS Transactions, 2010, 33, 235-241.	0.5	1
80	Heterogeneous Integration of LSI Amplifier and the Tactile Sensor Using Stacking and Through-Si-Via Techniques. Materials Research Society Symposia Proceedings, 2012, 1427, 14.	0.1	1
81	Passivation of Ge(100) and (111) Surfaces by Termination of Nonmetal Elements. Japanese Journal of Applied Physics, 2012, 51, 04DA06.	1.5	1
82	Force intensity and direction measurement in real time using miniature tactile sensor withl microcantilevers embedded in PDMS. , 2013, , .		1
83	Improvement in the Electrical Characteristics of a Fluorinated HfO2/Ge Gate Stack by Using a Nitrogen Radical Treatment. Journal of the Korean Physical Society, 2011, 59, 2503-2508.	0.7	1
84	<title>Surface treatment effects on Si(111) and (100) surface structures and Si/SiO2 interface state</title> . , 1998, , .		0
85	Preparation and characterization of ZrO/sub 2//Si structure. , 0, , .		0
86	BURST REACTION OF THIN FILMS EXCITED BY HIGH-FLUX SOFT X-RAYS. Surface Review and Letters, 2002, 09, 401-405.	1.1	0
87	Characterization of Ferroelectric Thin Film/SiO2/Si Structure by Photoreflectance. Ferroelectrics, 2004, 303, 119-123.	0.6	0
88	Data retention time of MFIS-FET memory structure improved with nitrogen and oxygen radical irradiation treatment. , 2006, , .		0
89	Fixed-Oxide-Charge Characterization by Photoreflec-tance Spectroscopy in HfO2 on Ge treated by Fluorine. ECS Transactions, 2009, 16, 699-705.	0.5	0
90	Structural and Ferroelectric Properties of Large c/a Phase Bismuth Ferrite Thin Films Prepared by Ion Beam Sputtering. Materials Research Society Symposia Proceedings, 2011, 1292, 3.	0.1	0

#	Article	IF	CITATIONS
91	Air damping effect on the air-based CMUT operation. Journal of the Korean Physical Society, 2015, 67, 486-495.	0.7	0
92	P(VDF-TeFE)/Organic Semiconductor Structure Ferroelectric-Gate FETs. Topics in Applied Physics, 2016, , 187-201.	0.8	0